

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ C$
-20V	90m Ω @ $V_{GS} = -4.5V$	-2.5A
	120m Ω @ $V_{GS} = -2.5V$	-2.0A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

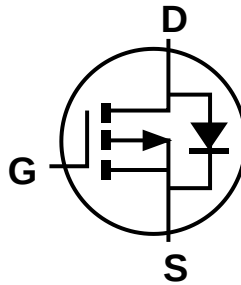
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)

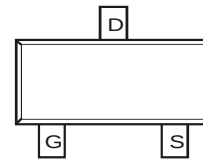
SOT323



Top View



Equivalent Circuit



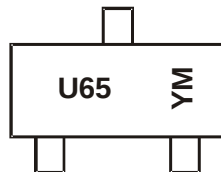
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2165UW-7	SOT323	3000/Tape & Reel
DMP2165UW-13	SOT323	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



U65 = Product Type Marking Code
YM or YM = Date Code Marking for SAT
Y or Y = Year (ex: F = 2018)
M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	-2.5 -2.0	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-1.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)	I _{DM}	-15	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	259	°C/W
Total Power Dissipation (Note 6)	P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	175	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	63	90	mΩ	V _{GS} = -4.5V, I _D = -1.5A
			83	120		V _{GS} = -2.5V, I _D = -1.2A
			160	180		V _{GS} = -1.8V, I _D = -1.2A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.1	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	335	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	72	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	32	—	pF	
Gate Resistance	R _G	—	15.5	—	Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	3.5	—	nC	V _{GS} = -4.5V, V _{DS} = -4V, I _D = -3.5A
Gate-Source Charge	Q _{gs}	—	0.4	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.7	—	ns	V _{DS} = -4V, V _{GS} = -4.5V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _R	—	8.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	17.8	—	ns	
Turn-Off Fall Time	t _F	—	8	—	ns	I _F = -4A, di/dt = 100A/μs
Reverse Recovery Time	t _{RR}	—	9	—	ns	
Reverse Recovery Charge	Q _{RR}	—	1.5	—	nC	I _F = -4A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

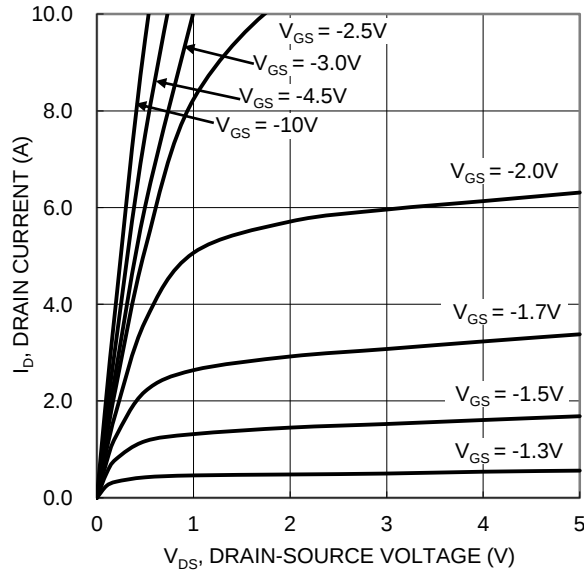


Figure 1. Typical Output Characteristic

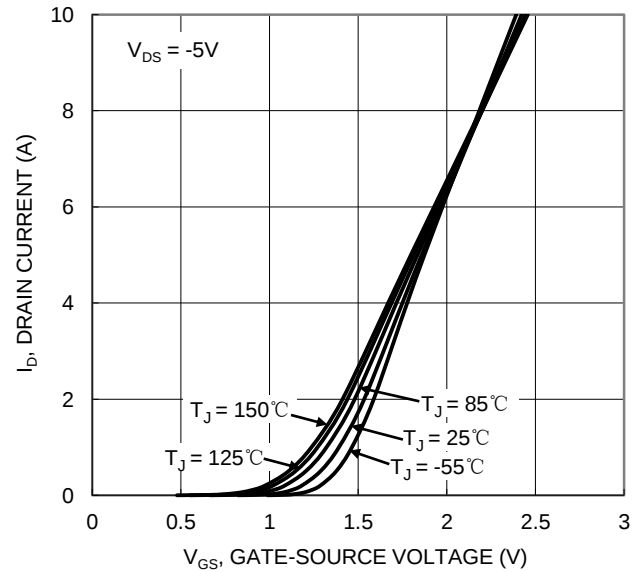


Figure 2. Typical Transfer Characteristic

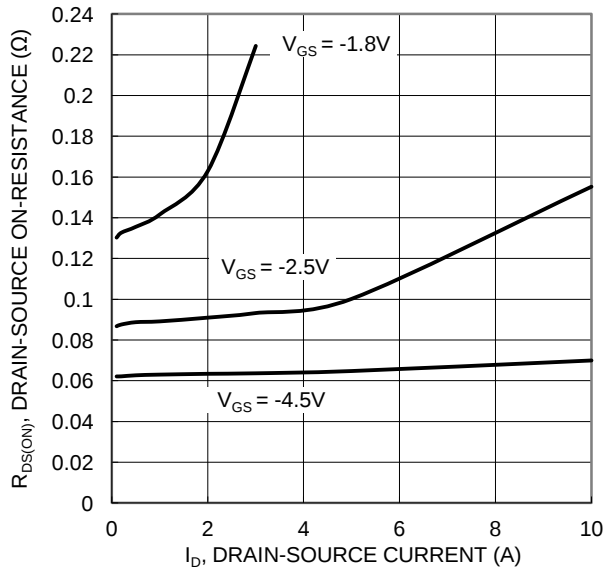


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

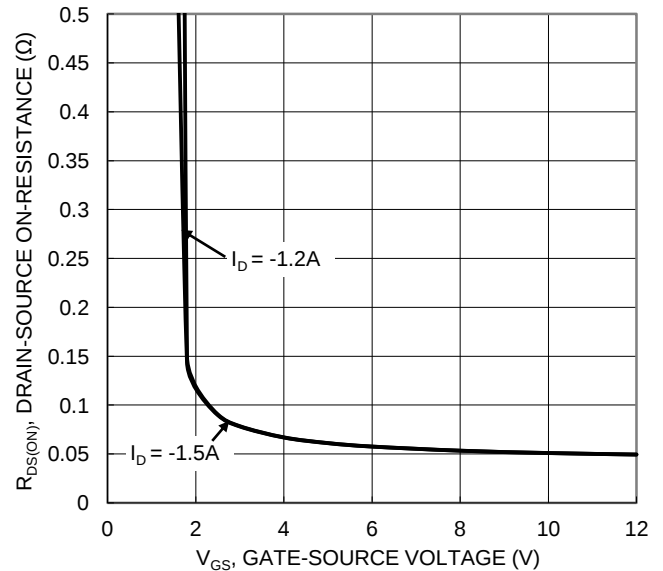


Figure 4. Typical Transfer Characteristic

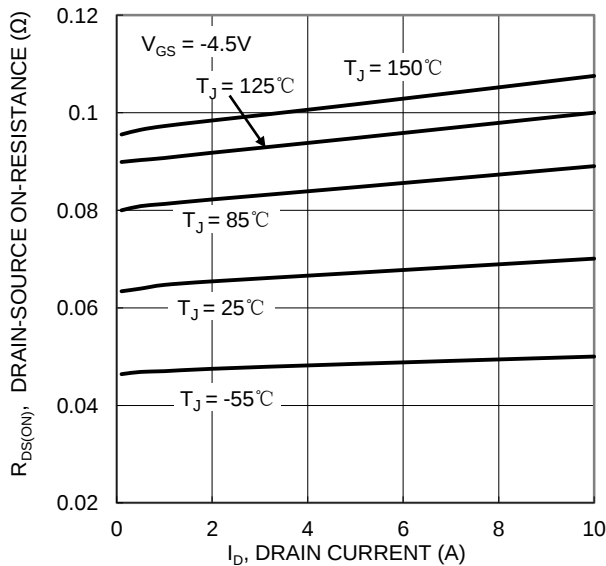


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

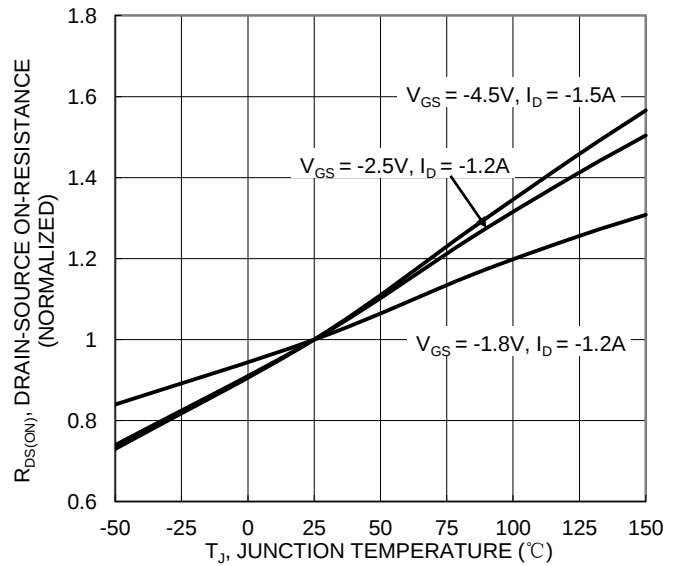


Figure 6. On-Resistance Variation with Junction Temperature

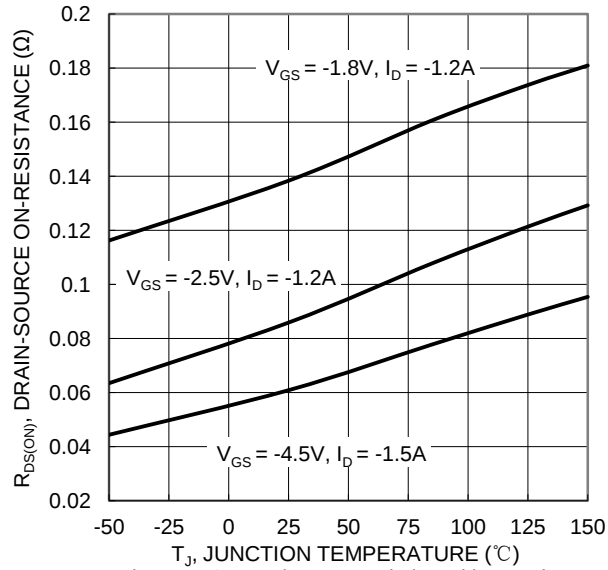


Figure 7. On-Resistance Variation with Junction Temperature

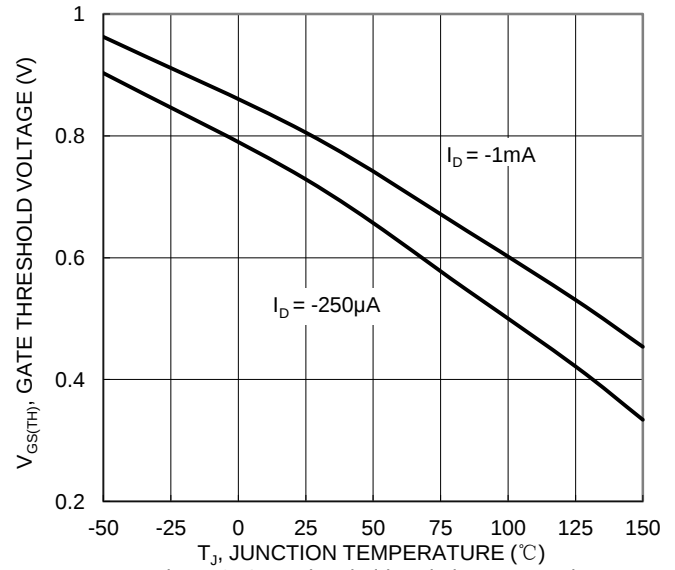


Figure 8. Gate Threshold Variation vs. Junction Temperature

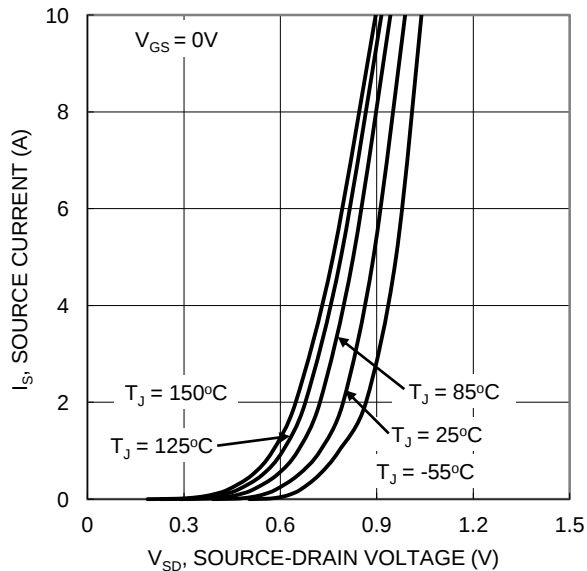


Figure 9. Diode Forward Voltage vs. Current

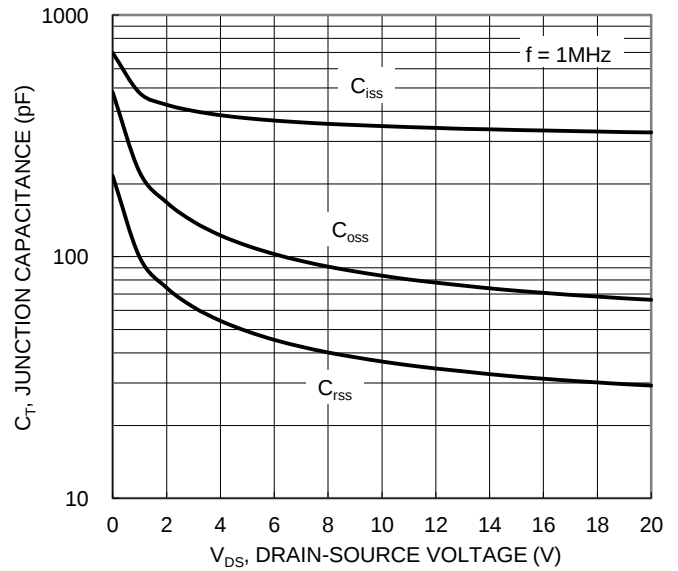


Figure 10. Typical Junction Capacitance

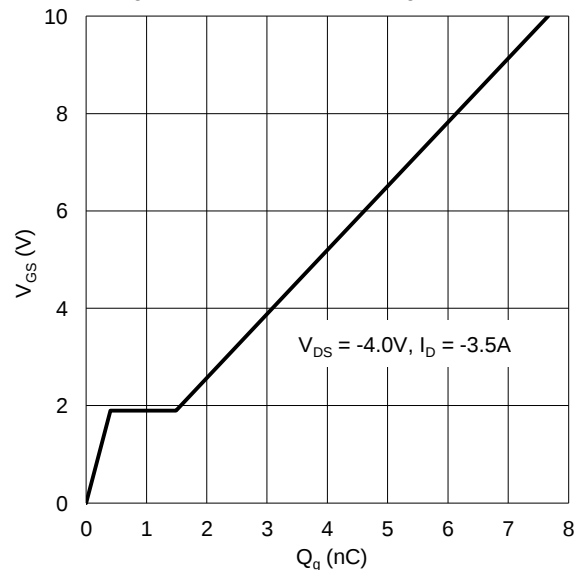


Figure 11. Gate Charge

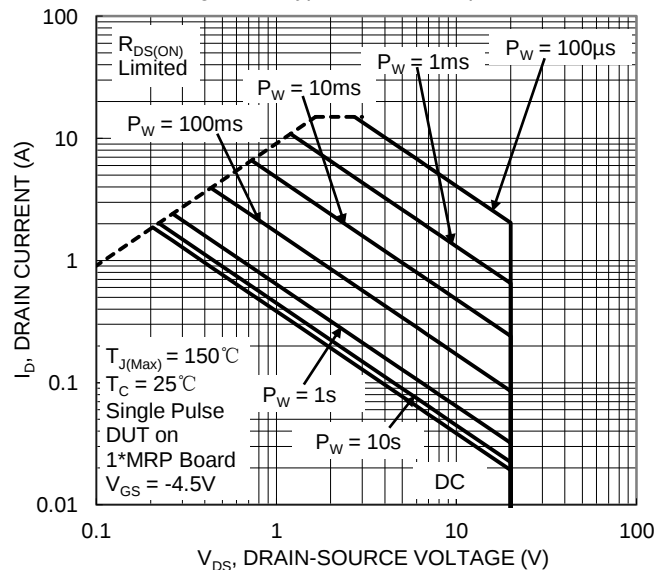


Figure 12. SOA, Safe Operation Area

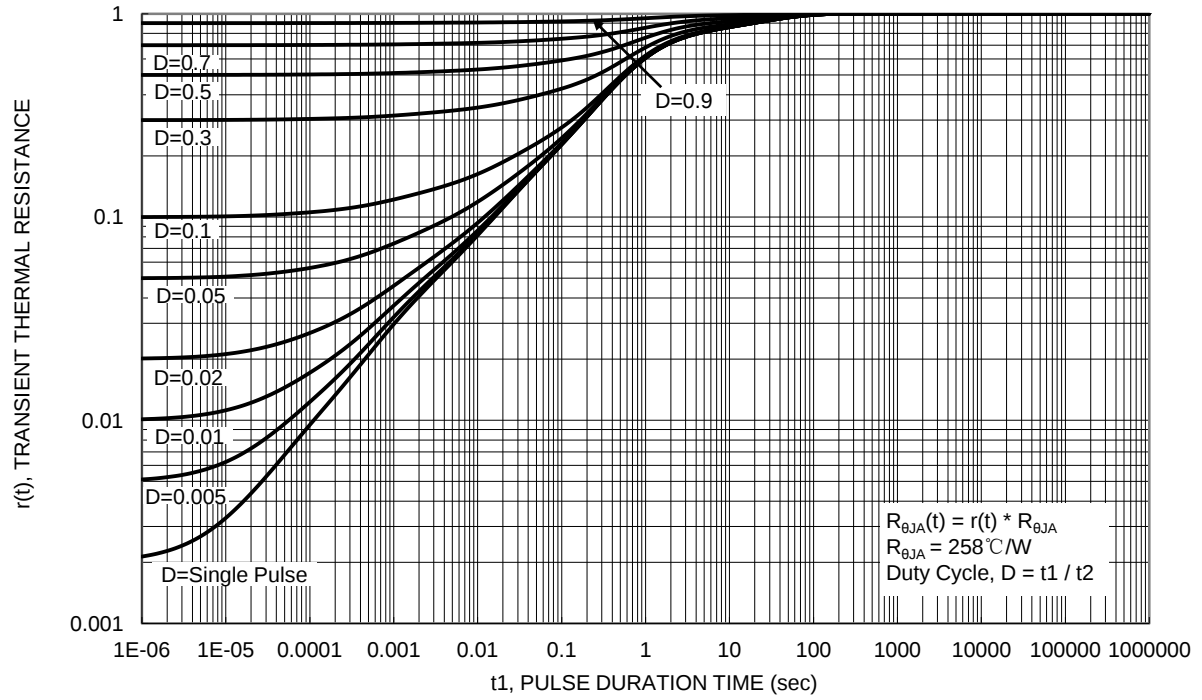
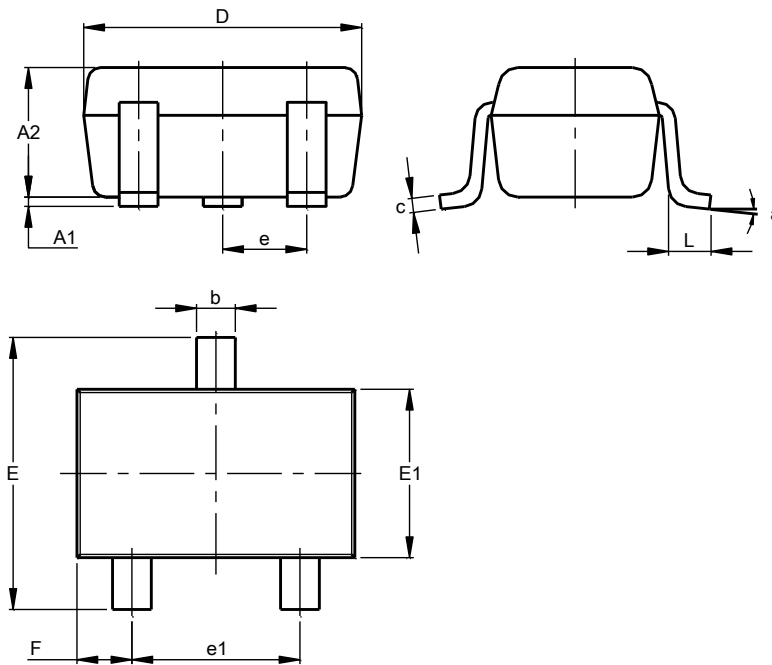


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323

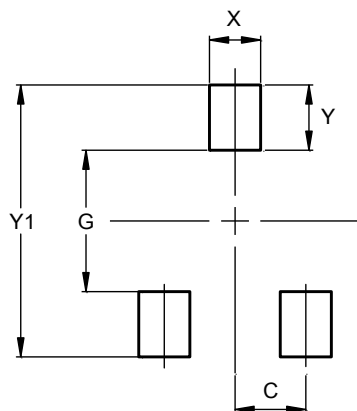


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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